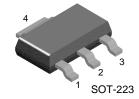


FZT3019

NPN General Purpose Amplifier

- This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 500 mA and collector voltages up to 80 V.
- Sourced from process 12.



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings* T_a=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CEO}	Collector-Emitter Voltage	80	V
V _{CBO}	Collector-Base Voltage	140	V
V _{EBO}	Emitter-Base Voltage	7.0	V
I _C	Collector Current - Continuous	7.0	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

^{*} This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These rating are based on a maximum junction temperature of 150 degrees C.
 These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

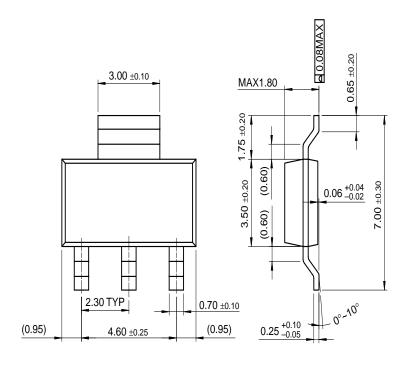
Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	teristics				
V _{(BR)CEO}	Collector-Emitter Sustaining Voltage *	$I_C = 30 \text{ mA}, I_B = 0$	80		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA, I _E = 0	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	7.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 90 \text{ V}, I_{E} = 0$ $V_{CB} = 90 \text{ V}, I_{E} = 0, T_{a} = 150^{\circ}\text{C}$		0.01 10	μA μA
I _{EBO}	Emitter-Cutoff Current			0.01	μΑ
On Charac	teristics				
h _{FE}	DC Current Gain	$\begin{split} I_{C} &= 0.1 \text{ mA, } V_{CE} = 10 \text{ V} \\ I_{C} &= 10 \text{ mA, } V_{CE} = 10 \text{ V} \\ I_{C} &= 150 \text{ mA, } V_{CE} = 10 \text{ V} \\ I_{C} &= 500 \text{ mA, } V_{CE} = 10 \text{ V} \\ I_{C} &= 1.0 \text{ A, } V_{CE} = 10 \text{ V} \end{split}$	50 90 100 50 15	300	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 500 mA, I _B = 15 V I _C = 1.0 A, I _B = 50 V		0.2 0.5	V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10 mA, I _B = 15 V		1.1	V
	al Characteristics			•	•
f _T	Current Gain - Bandwidth Product	I _C = 50 mA, V _{CE} = 10 V, f = 20 MHz	100		MHz
C _{cob}	Collector-Base Capacitance	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz		12	pF
C _{ibo}	Input Capacitance	V _{BE} = 10 V, I _E = 0, f = 1.0 MHz		60	pF
h _{fe}	Small Signal current Gain	$I_C = 50 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 20 MHz	80	400	
rb'Cc	Collector Base Time Constant	I _C = 10 mA, V _{CB} = 10 V, f = 4.0 MHz		400	pS
NF	Noise Figure	I_C = 100 mA, V_{CE} = 10 V, R_S = 1.0kΩ, f = 1.0KHz		4.0	dB

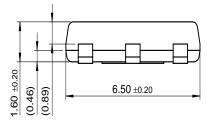
* Pulse Test: Pulse Width $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$

Thermal Characteristics T _a =25°C unless otherwise noted			
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

Package Dimensions

SOT-223





Dimensions in Millimeters

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E^2C	MOS™	HiSeC™	MSX TM	QT Optoelectronics™	TinyLogic [®]
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Acro	ss the board.	. Around the world.™	OCXPro™	RapidConnect™	UHC™
The Power Franchise®		OPTOLOGIC [®]	SILENT SWITCHER®	UltraFET [®]	
Programmable Active Droop™		OPTOPLANAR™	SMART START™	VCX TM	
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PRODUCT STATUS DEFINITIONS

Definition of Terms

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